

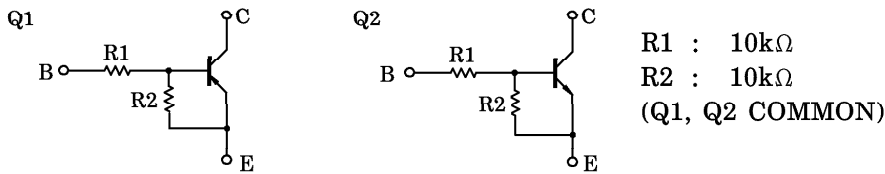
TOSHIBA TRANSISTOR
SILICON PNP EPITAXIAL TYPE (PCT PROCESS) SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

RN4602

SWITCHING, INVERTER CIRCUIT, INTERFACE CIRCUIT
AND DRIVER CIRCUIT APPLICATIONS.

- Including Two Devices in SM6 (Super Mini Type with 6 leads)
- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process

EQUIVALENT CIRCUIT AND BIAS RESISTOR VALUES



Q1 MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-10	V
Collector Current	I_C	-100	mA

Q2 MAXIMUM RATINGS (Ta = 25°C)

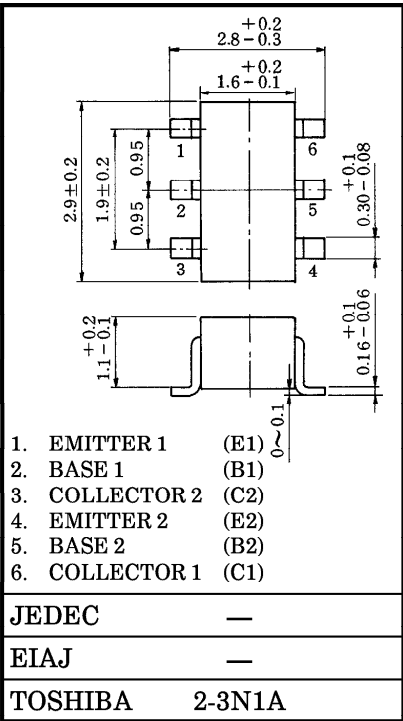
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	100	mA

Q1, Q2 COMMON MAXIMUM RATINGS (Ta = 25°C)

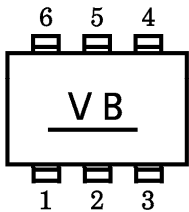
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	P_C^*	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

* : Total Rating

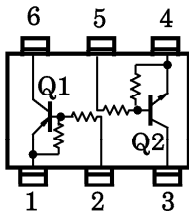
Unit in mm



MARKING



EQUIVALENT CIRCUIT (TOP VIEW)



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Q1 ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	V _{CB} = -50V, I _E = 0	—	—	-100	nA
	ICEO	V _{CE} = -50V, I _B = 0	—	—	-500	
Emitter Cut-off Current	I _{EBO}	V _{EB} = -10V, I _C = 0	-0.82	—	-1.52	mA
DC Current Gain	h _{FE}	V _{CE} = -5V, I _C = -10mA	30	—	—	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -5mA, I _B = -0.25mA	—	-0.1	-0.3	V
Input Voltage (ON)	V _{I(ON)}	V _{CE} = -0.2V, I _C = -5mA	-1.1	—	-2.0	V
Input Voltage (OFF)	V _{I(OFF)}	V _{CE} = -5V, I _C = -0.1mA	-1.0	—	-1.5	V
Transition Frequency	f _T	V _{CE} = -10V, I _C = -5mA	—	200	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	3	6	pF

Q2 ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	V _{CB} = 50V, I _E = 0	—	—	100	nA
	ICEO	V _{CE} = 50V, I _B = 0	—	—	500	
Emitter Cut-off Current	I _{EBO}	V _{EB} = 10V, I _C = 0	0.82	—	1.52	mA
DC Current Gain	h _{FE}	V _{CE} = 5V, I _C = 10mA	30	—	—	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 5mA, I _B = 0.25mA	—	0.1	0.3	V
Input Voltage (ON)	V _{I(ON)}	V _{CE} = 0.2V, I _C = 5mA	1.1	—	2.0	V
Input Voltage (OFF)	V _{I(OFF)}	V _{CE} = 5V, I _C = 0.1mA	1.0	—	1.5	V
Transition Frequency	f _T	V _{CE} = 10V, I _C = 5mA	—	250	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	3	6	pF

Q1, Q2 COMMON ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Resistor	R1		3.29	4.7	6.11	kΩ
Resistor Ratio	R1/R2		0.9	1.0	1.1	

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